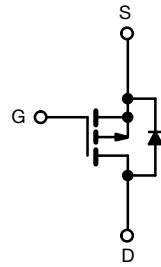
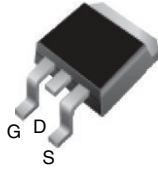


Power MOSFET

D²PAK (TO-263)


P-Channel MOSFET

FEATURES

- Advanced process technology
- Surface mount (IRF9Z34S, SiHF9Z34S)
- 175 °C operating temperature
- Fast switching
- P-channel
- Fully avalanche rated
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS*
Available
HALOGEN
FREE
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

DESCRIPTION

Third generation power MOSFETs from Vishay utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²PAK is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²PAK is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface mount application.

PRODUCT SUMMARY		
V _{DS} (V)	-60	
R _{DS(on)} (Ω)	V _{GS} = -10 V	0.14
Q _g max. (nC)	34	
Q _{gs} (nC)	9.9	
Q _{gd} (nC)	16	
Configuration	Single	

ORDERING INFORMATION			
Package	D ² PAK (TO-263)	D ² PAK (TO-263)	D ² PAK (TO-263)
Lead (Pb)-free and Halogen-free	-	SiHF9Z34STRL-GE3 ^a	SiHF9Z34STRR-GE3 ^a
Lead (Pb)-free	IRF9Z34SPbF	IRF9Z34STRLPbF ^a	IRF9Z34STRRPbF ^a

Note

a. See device orientation

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)				
PARAMETER	SYMBOL		LIMIT	UNIT
Drain-Source Voltage	V _{DS}		-60	V
Gate-Source Voltage	V _{GS}		± 20	
Continuous Drain Current	V _{GS} at -10 V	T _C = 25 °C	-18	A
		T _C = 100 °C	-13	
Pulsed Drain Current ^{a, e}	I _{DM}		-72	
Linear Derating Factor			0.59	W/°C
Single Pulse Avalanche Energy ^{b, e}	E _{AS}		370	mJ
Avalanche Current ^a	I _{AR}		-18	A
Repetitive Avalanche Energy ^a	E _{AR}		8.8	mJ
Maximum Power Dissipation	T _C = 25 °C		88	W
	T _A = 25 °C		3.7	
Peak Diode Recovery dV/dt ^{c, e}	dV/dt		-4.5	V/ns
Operating Junction and Storage Temperature Range	T _J , T _{stg}		-55 to +175	°C
Soldering Recommendations (Peak temperature) ^d	for 10 s		300	

Notes


- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- V_{DD} = -25 V, starting T_J = 25 °C, L = 1.3 mH, R_g = 25 Ω, I_{AS} = -18 A (see fig. 12)
- I_{SD} ≤ -18 A, di/dt ≤ 170 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 175 °C
- 1.6 mm from case
- Uses IRF9Z34, SiHF9Z34 data and test conditions



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB mounted, steady-state) ^a	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	1.7	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material)

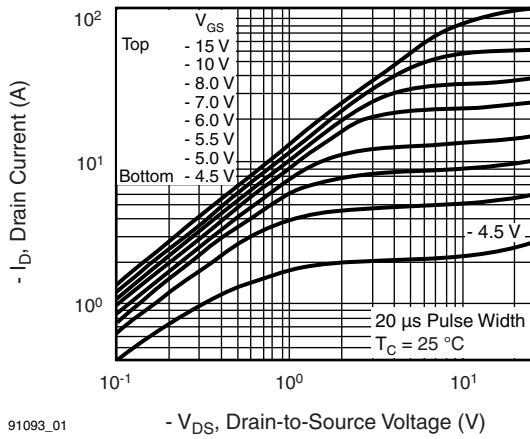
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$	-60	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = -1\text{ mA}$ ^c	-	-0.06	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	-2.0	-	-4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	-100	μA
		$V_{DS} = -48\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$	-	-	-500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$ $I_D = -11\text{ A}$ ^b	-	-	0.14	Ω
Forward Transconductance	g_{fs}	$V_{DS} = -25\text{ V}$, $I_D = -11\text{ A}$ ^c	5.9	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = -25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5 ^c	-	1100	-	μF
Output Capacitance	C_{oss}		-	620	-	
Reverse Transfer Capacitance	C_{rss}		-	100	-	
Total Gate Charge	Q_g	$V_{GS} = -10\text{ V}$ $I_D = -18\text{ A}$, $V_{DS} = -48\text{ V}$, see fig. 6 and 13 ^{b, c}	-	-	34	nC
Gate-Source Charge	Q_{gs}		-	-	9.9	
Gate-Drain Charge	Q_{gd}		-	-	16	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -30\text{ V}$, $I_D = -18\text{ A}$, $R_g = 12\text{ }\Omega$, $R_D = 1.5\text{ }\Omega$, see fig. 10 ^{b, c}	-	18	-	ns
Rise Time	t_r		-	120	-	
Turn-Off Delay Time	$t_{d(off)}$		-	20	-	
Fall Time	t_f		-	58	-	
Gate Input Resistance	R_g	$f = 1\text{ MHz}$, open drain	0.7	-	3.9	Ω
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p-n junction diode 	-	-	-18	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	-72	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}$, $I_S = -18\text{ A}$, $V_{GS} = 0\text{ V}$ ^b	-	-	-6.3	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $I_F = -18\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$ ^{b, c}	-	100	200	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	280	520	nC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- b. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
c. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$
d. Uses IRF9Z34, SiHF9Z34 data and test conditions

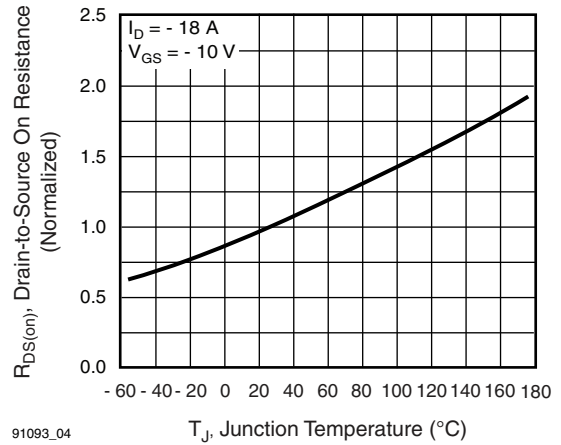


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



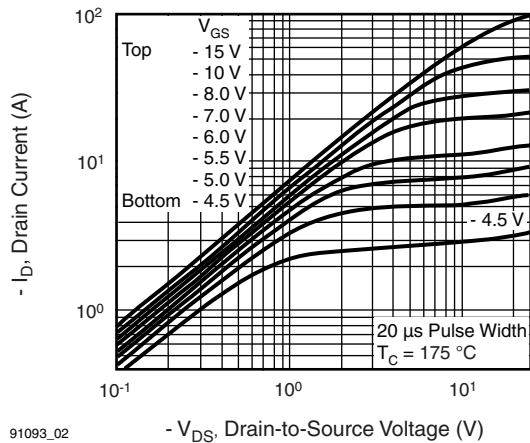
91093_01

Fig. 1 - Typical Output Characteristics



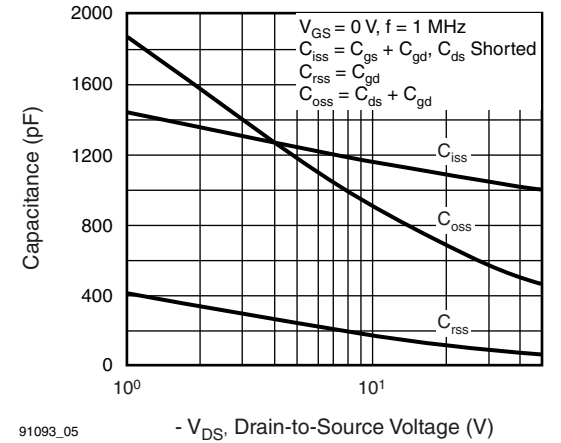
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Fig. 4 - Normalized On-Resistance vs. Temperature



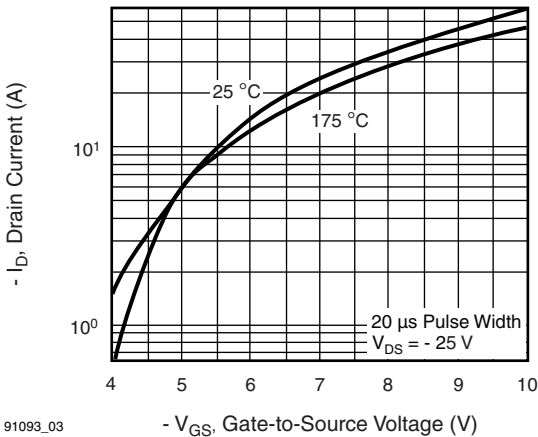
91093_02

Fig. 2 - Typical Output Characteristics



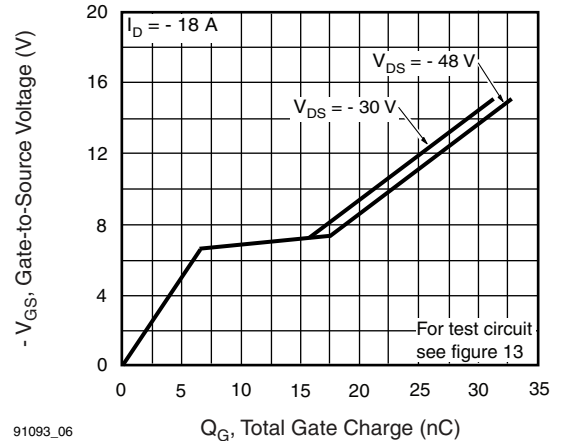
91093_05

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



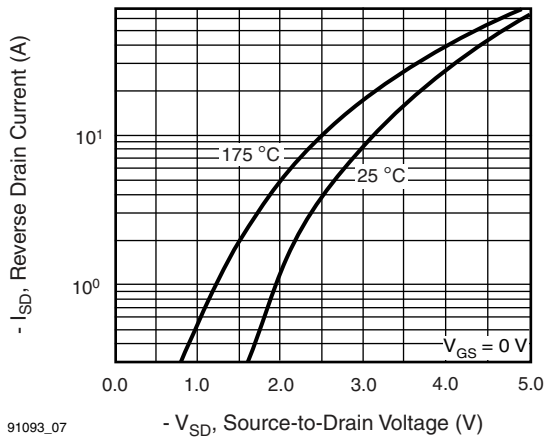
91093_03

Fig. 3 - Typical Transfer Characteristics



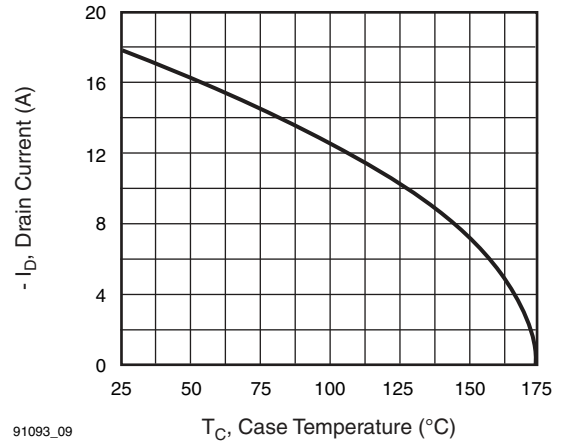
91093_06

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



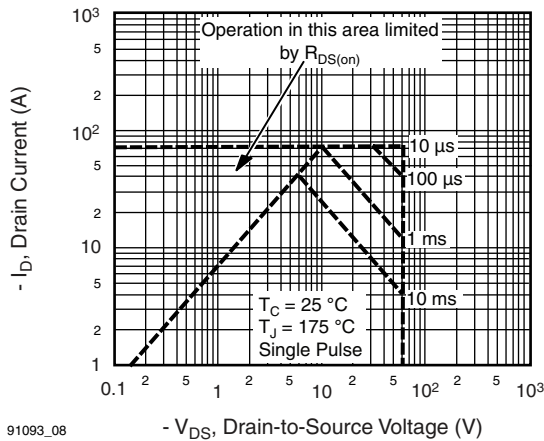
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



91093_09

Fig. 9 - Maximum Drain Current vs. Case Temperature



91093_08

Fig. 8 - Maximum Safe Operating Area

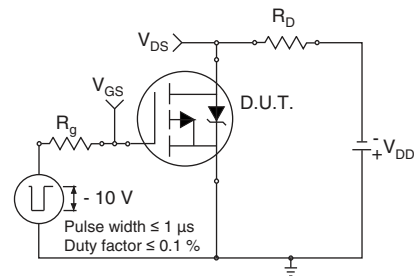


Fig. 10a - Switching Time Test Circuit

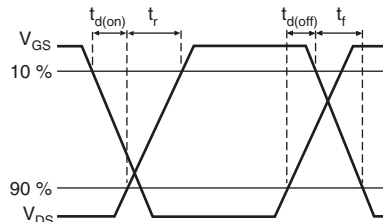
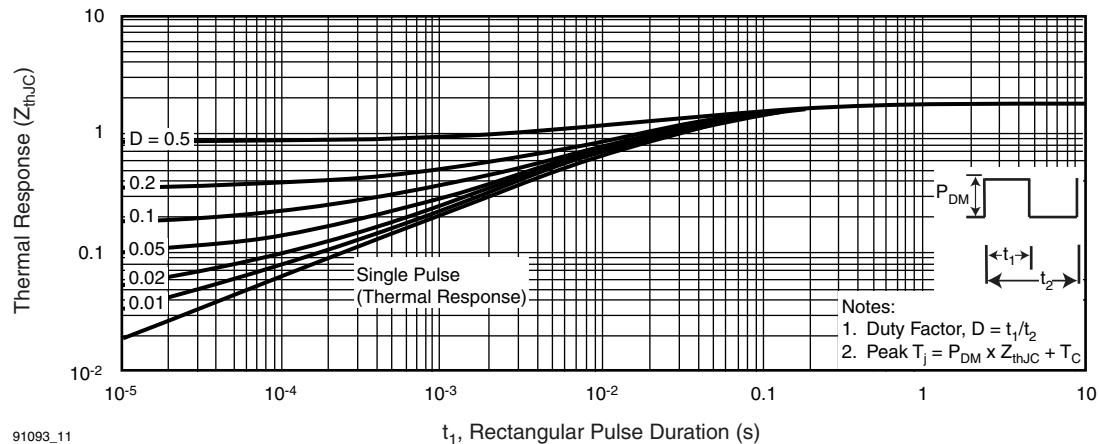


Fig. 10b - Switching Time Waveforms



91093_11

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

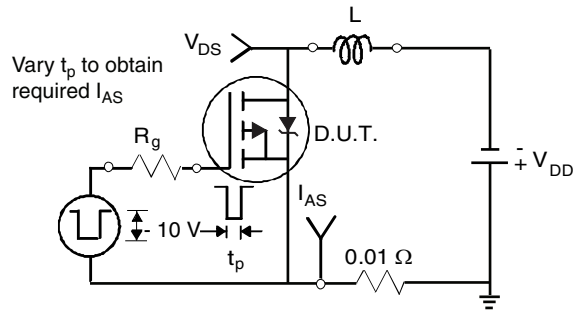


Fig. 12a - Unclamped Inductive Test Circuit

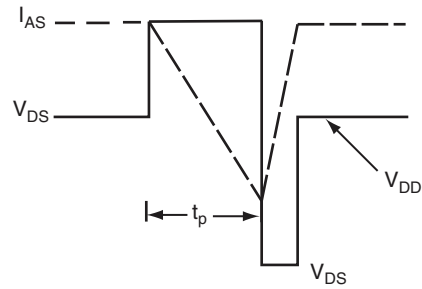
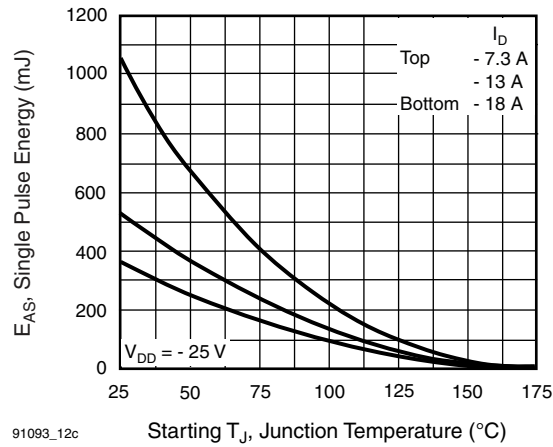


Fig. 12b - Unclamped Inductive Waveforms



91093_12c

Fig. 12c - Maximum Avalanche Energy vs. Drain Current

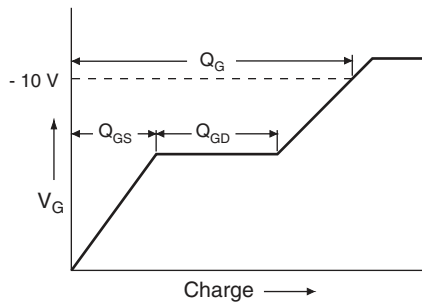


Fig. 13 - Maximum Avalanche Energy vs. Drain Current

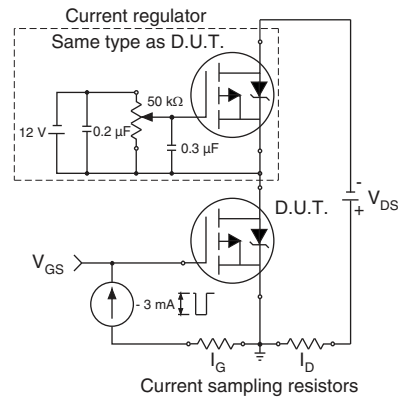


Fig. 13b - Gate Charge Test Circuit

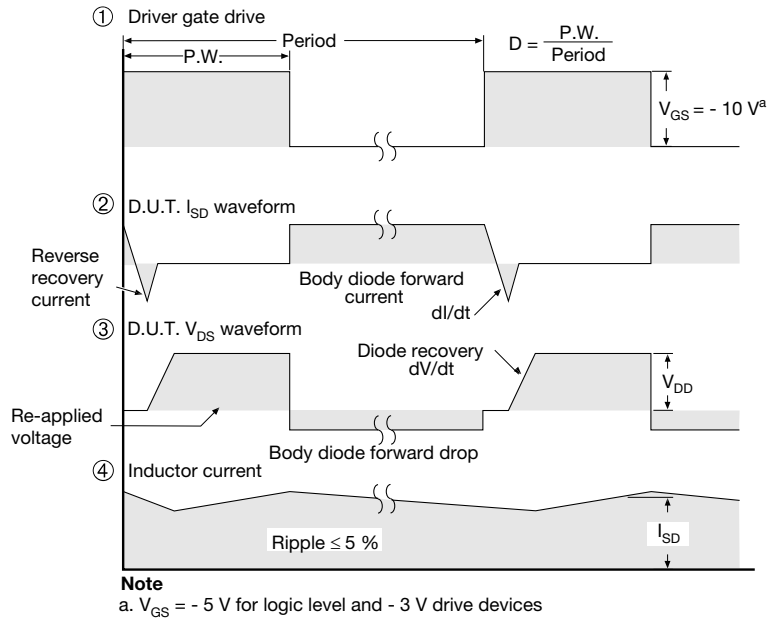
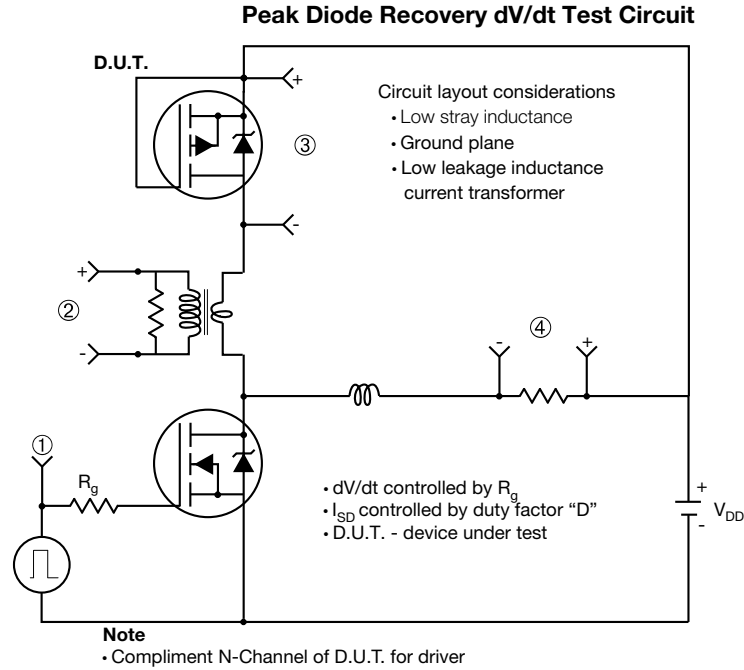


Fig. 14 - For P-Channel

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TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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